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Data Sheet

Preliminary

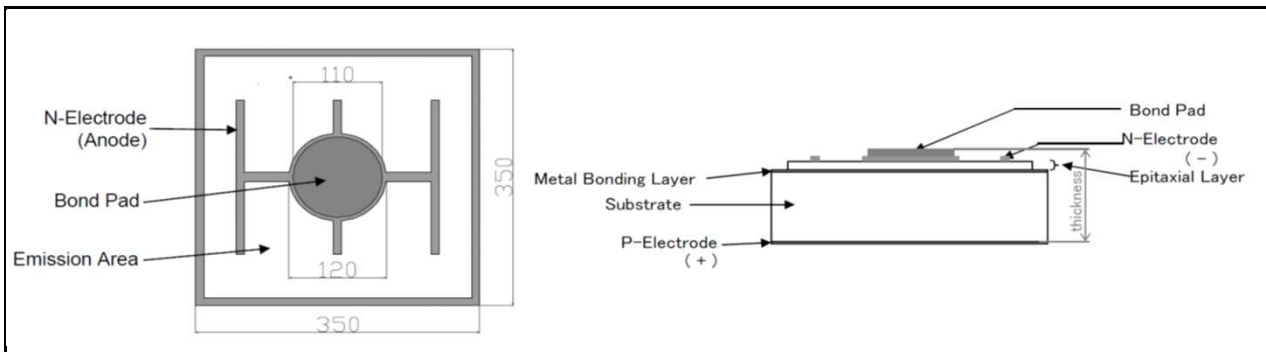
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Infrared LED Chip

EOLC-1200-27D

Rev. 01, 2018

Radiation	Type	Electrodes
Infrared	InGaAs - based material	n (cathode) up



Die size (typ.): 0.350 mm × 0.350 mm (14 mil)

Thickness (typ.): 0.180 mm (7 mil)

Bond pad size: Ø 0.110 mm (periphery = Ø 0.120 mm)

Contact metallization: gold alloy

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.0		V
Radiant power*	$I_F = 20 \text{ mA}$	Φ_e		2.8		mW
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p		1220		nm

*Measured on bare chip on TO-18 header

Packing

Dice on adhesive film with wire bond side up.

Art. No. 113 xxx



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.